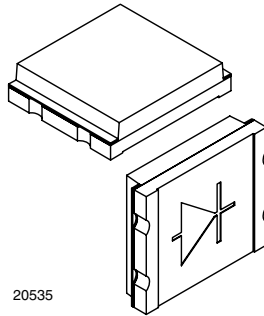


## Silicon PIN Photodiode



### DESCRIPTION

TEMD5080X01 is a PIN photodiode with enhanced blue sensitivity. The miniature surface mount package (SMD) include a chip with 7.7 mm<sup>2</sup> sensitive area, covered by clear epoxy.

### FEATURES

- Package type: surface mount
- Package form: top view
- Dimensions (L x W x H in mm): 5 x 4.24 x 1.12
- Radiant sensitive area (in mm<sup>2</sup>): 7.7
- AEC-Q101 qualified
- Enhanced blue photo sensitivity: S (400 nm) rel > 30 %
- Peak sensitivity at 940 nm
- Suitable for visible and near infrared radiation
- Low junction capacitance
- Fast response times
- Angle of half sensitivity:  $\phi = \pm 65^\circ$
- Floor life: 72 h, MSL 4, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Find out more about Vishay's Automotive Grade Product requirements at: [www.vishay.com/applications](http://www.vishay.com/applications)


**RoHS**  
COMPLIANT


### APPLICATIONS

- High speed photo detector

### PRODUCT SUMMARY

COMPONENT	$I_{ra}$ ( $\mu$ A)	$\phi$ (deg)	$\lambda_{0.1}$ (nm)
TEMD5080X01	60	$\pm 65$	350 to 1100

#### Note

Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TEMD5080X01	Tape and reel	MOQ: 1500 pcs, 1500 pcs/reel	Top view

#### Note

MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	25	V
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	$P_V$	215	mW
Junction temperature		$T_j$	100	$^\circ\text{C}$
Operating temperature range		$T_{amb}$	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	- 40 to + 110	$^\circ\text{C}$
Soldering temperature	Acc. reflow solder profile fig. 8	$T_{sd}$	260	$^\circ\text{C}$
Thermal resistance junction/ambient		$R_{thJA}$	350	K/W

#### Note

$T_{amb} = 25^\circ\text{C}$ , unless otherwise specified

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50 \text{ mA}$	$V_F$		1	1.3	V
Breakdown voltage	$I_R = 100 \text{ }\mu\text{A}, E = 0$	$V_{(BR)}$	25			V
Reverse dark current	$V_R = 10 \text{ V}, E = 0$	$I_{ro}$		2	10	nA
Diode capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}, E = 0$	$C_D$		90		pF
	$V_R = 3 \text{ V}, f = 1 \text{ MHz}, E = 0$	$C_D$		30	40	pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	$V_o$		350		mV
Temperature coefficient of $V_o$	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	$TK_{V_o}$		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	$I_k$		50		$\mu\text{A}$
Temperature coefficient of $I_k$	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	$TK_{I_k}$		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 400 \text{ nm}, V_R = 5 \text{ V}$	$I_{ra}$		18		$\mu\text{A}$
	$E_v = 100 \text{ lx}, \text{CIE illuminant A}, V_R = 5 \text{ V}$	$I_{ra}$		8.5		$\mu\text{A}$
	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_R = 5 \text{ V}$	$I_{ra}$		60		$\mu\text{A}$
Temperature coefficient of $I_{ra}$	CIE illuminant A	$TK_{I_{ra}}$		0.15		%/K
	$\lambda = 950 \text{ nm}$	$TK_{I_{ra}}$		0.1		%/K
Angle of half sensitivity		$\phi$		$\pm 65$		deg
Wavelength of peak sensitivity		$\lambda_p$		940		nm
Range of spectral bandwidth		$\lambda_{0.1}$		350 to 1100		nm
Noise equivalent power	$V_R = 10 \text{ V}, \lambda = 400 \text{ nm}$	NEP		$1.1 \times 10^{-13}$		$\text{W}/\sqrt{\text{Hz}}$
Rise time	$V_R = 5 \text{ V}, R_L = 50 \text{ }\Omega, \lambda = 850 \text{ nm}$	$t_r$		40		ns
Fall time	$V_R = 5 \text{ V}, R_L = 50 \text{ }\Omega, \lambda = 850 \text{ nm}$	$t_f$		40		ns

**Note**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

**BASIC CHARACTERISTICS**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

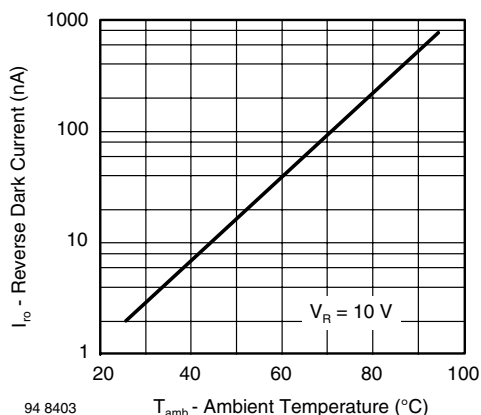


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

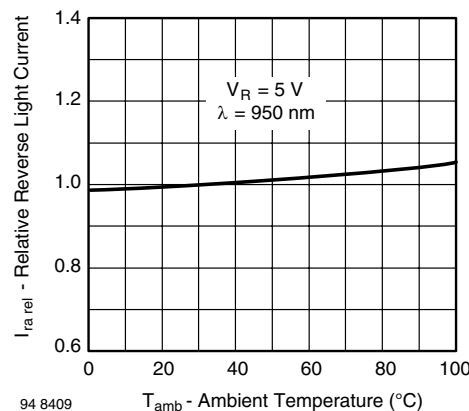


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

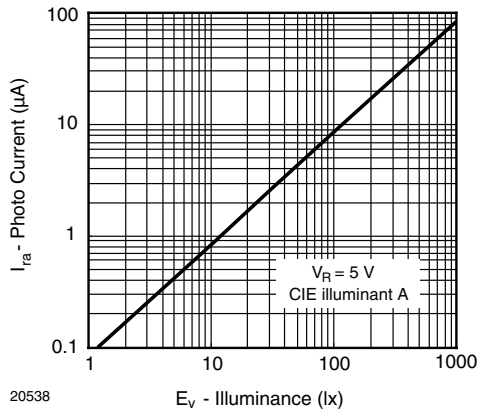


Fig. 3 - Reverse Light Current vs. Irradiance

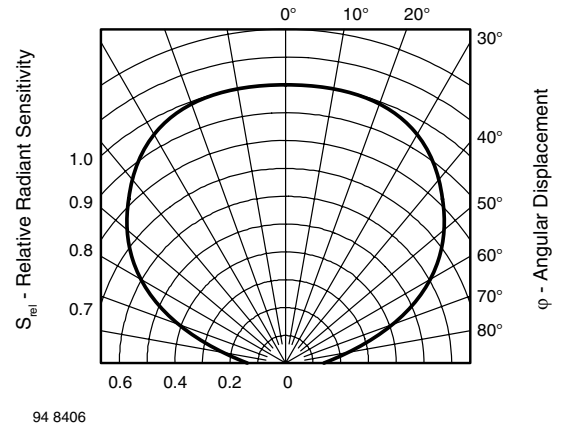


Fig. 6 - Relative Radiant Sensitivity vs. Angular Displacement

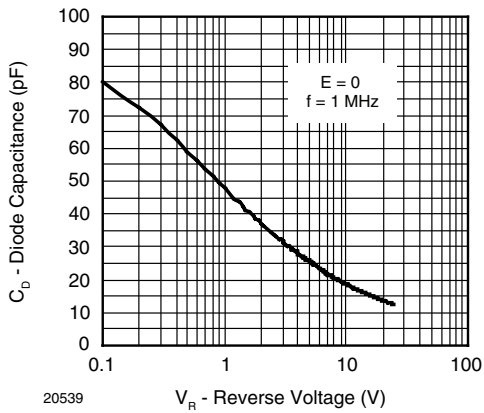


Fig. 4 - Diode Capacitance vs. Reverse Voltage

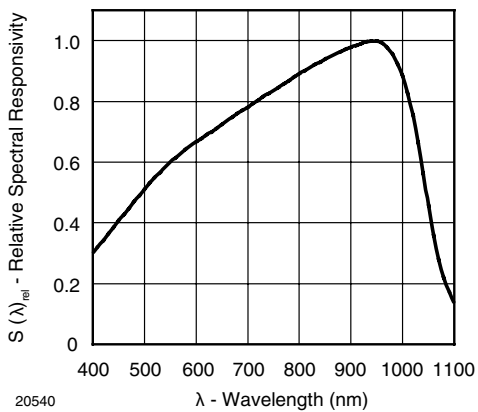


Fig. 5 - Relative Spectral Sensitivity vs. Wavelength

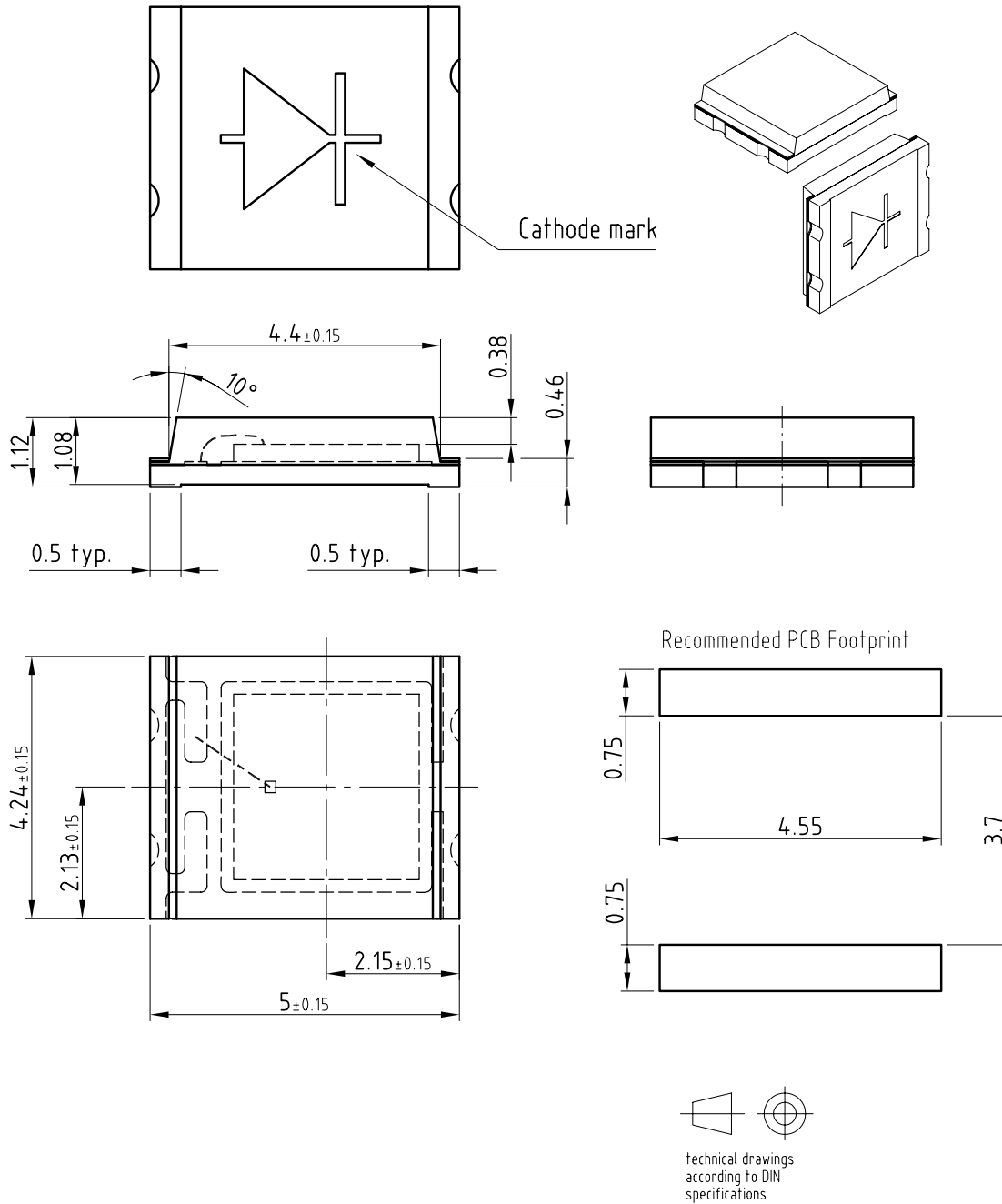
# TEMD5080X01

Vishay Semiconductors

Silicon PIN Photodiode



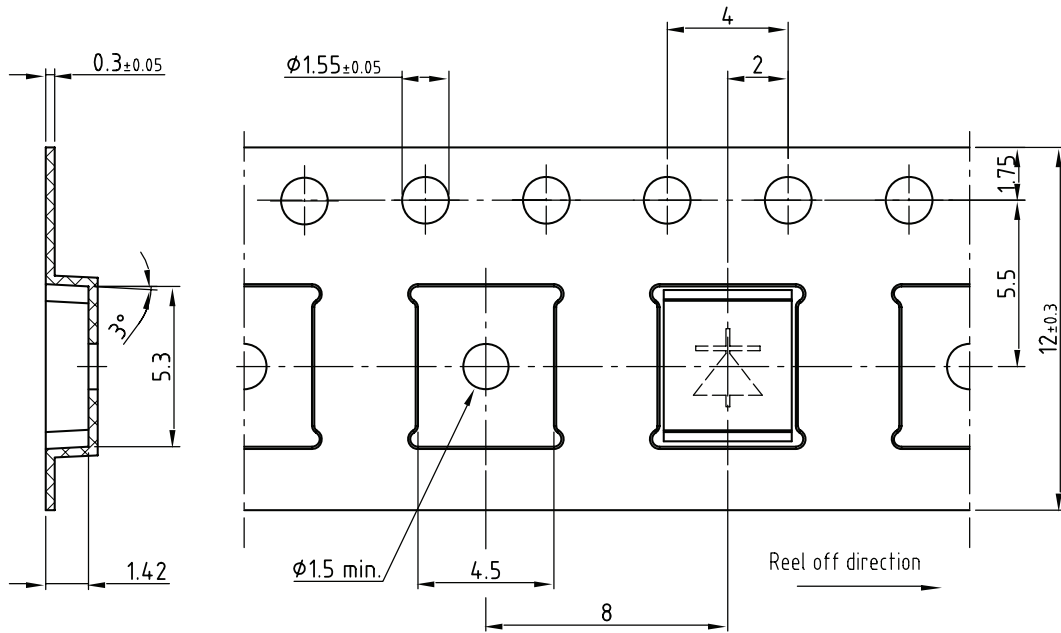
## PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.541-5060.01-4  
Issue: 3; 05.02.08  
20536

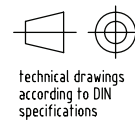
Not indicated tolerances  $\pm 0.1$

**TAPING DIMENSIONS** in millimeters

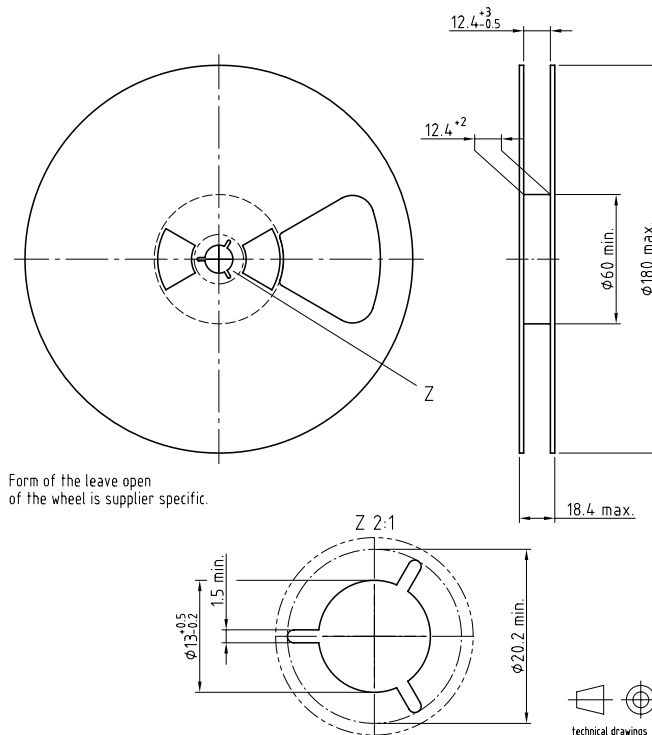


Drawing-No.: 9.700-5293.01-4  
Issue: 1; 03.12.04  
20537

Not indicated tolerances ±0.1



**REEL DIMENSIONS** in millimeters



Form of the leave open of the wheel is supplier specific.

Drawing-No.: 9.800-5097.01-4  
Issue: 1; 05.05.08  
20874



## SOLDER PROFILE

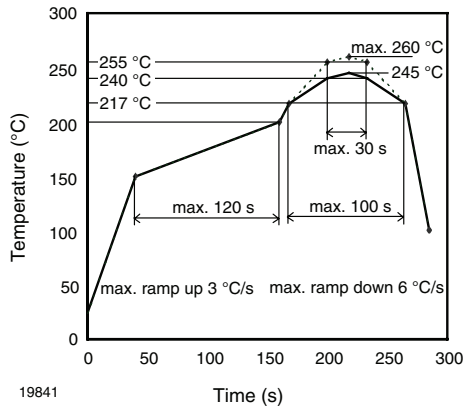


Fig. 7 - Lead (Pb)-free Reflow Solder Profile  
acc. J-STD-020D

## DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

## FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 4

Floor life: 72 h

Conditions:  $T_{amb} < 30\text{ °C}$ ,  $RH < 60\%$

## DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions:

192 h at  $40\text{ °C} (+ 5\text{ °C})$ ,  $RH < 5\%$

or

96 h at  $60\text{ °C} (+ 5\text{ °C})$ ,  $RH < 5\%$ .



## Disclaimer

All product specifications and data are subject to change without notice.

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